

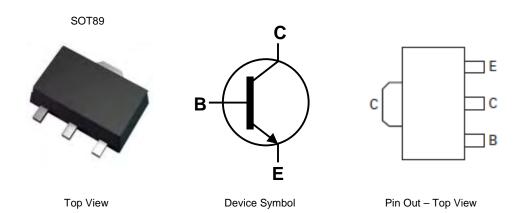
32V NPN SUFACE MOUNT TRANSISTOR IN SOT89

Features

- BV_{CEO} > 32V
- Max Continuous Current I_C = 1A
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (2DB1132)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.055 grams (Approximate)



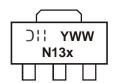
Ordering Information (Note 4)

I	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	2DD1664P-13	N13P	13	12	2,500
	2DD1664Q-13	N13Q	13	12	2,500
	2DD1664R-13	N13R	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

Marking Information



N13x = Product Type Marking Code:
Where N13P = 2DD1664

Where N13P = 2DD1664P N13Q = 2DD1664Q

N13R = 2DD1664R

YWW = Date Code Marking Y = Last digit of year ex: 1 = 2011 WW = Week code (01 – 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	32	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current (Note 6)	I _{CM}	2	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	22	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C

Notes:

- 5. For a device surface mounted on FR-4 PCB with minimum suggested pad layout; high coverage of single sided 1 oz copper, in still air conditions
- 6. Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.

 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

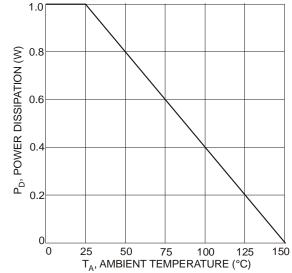


Figure 1. Power Dissipation vs. Ambient Temperature

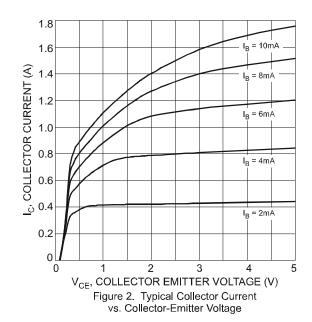


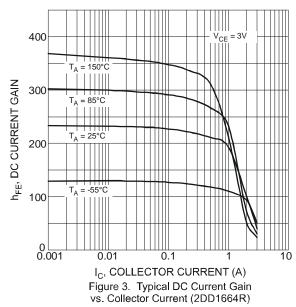
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV_CBO	40	-	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 8)		BV _{CEO}	32	-	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage		BV _{EBO}	6	-	-	V	I _E = 100μA
Collector-Emitter Cut-off Current		I _{CES}	-	-	100	nA	V _{CE} = 32V
Collector-Base Cut-off Current		I _{CBO}	-	-	100	nA	V _{CB} = 36V
Base-Emitter Cut-off Current		I _{EBO}	-	-	100	nA	$V_{EB} = 6V$
Static Forward Current Transfer	2DD1664P		82		180		
Ratio (Note 8)	2DD1664Q	h _{FE}	120	-	270	-	$I_C = 100 \text{mA}, V_{CE} = 3 \text{V}$
Italio (Note o)	2DD1664R		180		390		
Collector-Emitter saturation Voltage (Note 8)		V _{CE(sat)}	-	120	400	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Transition frequency		f _T	-	280	-	MHz	$I_E = 50 \text{mA}, V_{CE} = 5 \text{V}, f = 30 \text{MHz}$
Output Capacitance		C_ob	-	10	-	pF	$I_E = 0A$, $V_{CB} = 10V$, $f = 1MHz$

Notes: 8. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







Electrical Characteristics (cont.) (@T_A = +25°C, unless otherwise specified.)

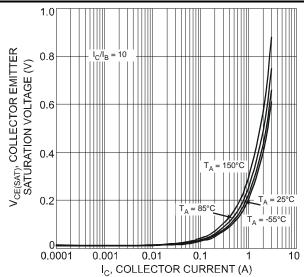
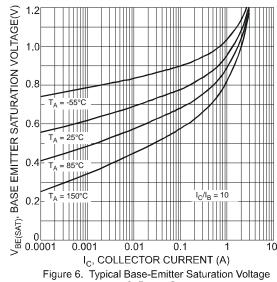


Figure 4. Typical Collector-Emitter Saturation Voltage vs. Collector Current



vs. Collector Current

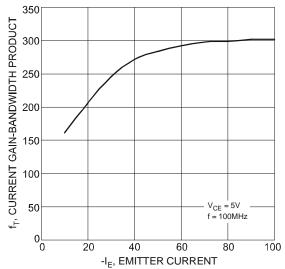


Figure 8. Typical Gain-Bandwidth Product vs. Emitter Current

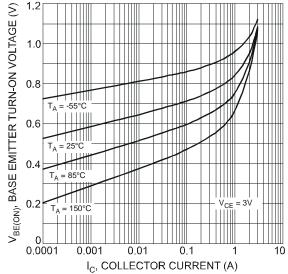


Figure 5. Typical Base-Emitter Turn-On Voltage vs. Collector Current

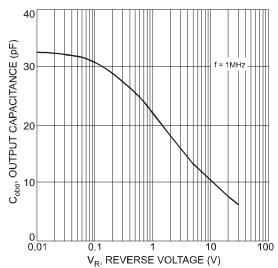
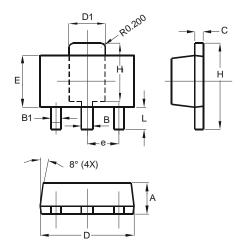


Figure 7. Typical Output Capacitance Characteristics

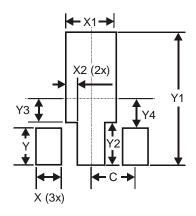


Package Outline Dimensions



	SOT89					
Dim	Min	Max				
Α	1.40	1.60				
В	0.44	0.62				
B1	0.35	0.54				
С	0.35	0.44				
D	4.40	4.60				
D1	1.62	1.83				
Е	2.29	2.60				
е	1.50 Typ					
Н	3.94	4.25				
H1	2.63	2.93				
L	0.89	1.20				
All [All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1 500



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